Power LDMOS transistor

AMPLEON

Rev. 2 — 8 July 2022

Product data sheet

1. Product profile

1.1 General description

Based on Advanced Rugged Technology (ART) a 35 W LDMOS transistor for ISM application has been designed. This unmatched device covers a frequency range of 1 MHz to 650 MHz.

Table 1. Application information

Test signal	f	V _{DS}	PL	Gp	ησ
	(MHz)	(V)	(W)	(dB)	(%)
CW pulsed [1][2]	108	65	35	30.4	71.2
CW [3]	10 to 54	65	35	28.7	75.3
CW [3]	60 to 130	65	35	24.6	65.8
CW [3]	81 to 108	65	35	30.1	72.7

^[1] $t_p = 100 \,\mu\text{s}; \, \delta = 10 \,\%.$

1.2 Features and benefits

- High breakdown voltage enables class E operation up to V_{DS} = 53 V
- Qualified up to a maximum of V_{DS} = 65 V
- Characterized from 30 V to 65 V to support a wide range of applications
- Easy power control
- Integrated dual sided ESD protection enables class C operation and complete switch off of the transistor
- Excellent ruggedness with no device degradation
- High efficiency
- Excellent thermal stability
- Designed for broadband operation
- For RoHS compliance see the product details on the Ampleon website

^[2] Production circuit.

^[3] Center band performance numbers across the indicated frequency range.

1.3 Applications

- Industrial, scientific and medical applications
 - Plasma generators
 - MRI systems
 - ◆ CO₂ lasers
 - ◆ Particle accelerators
- Broadcast
 - FM radio
 - VHF TV
- Radar
 - ◆ Non cellular communications
 - UHF radar

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain			,
2	gate		1	1
3	source	[1]	3	2 —
			2	3 sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC		Min. orderable quantity (pieces)
SOT467C	ART35FEU	9349 603 46112	Tray; 20-fold; non-dry pack	20

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	[1]	-	200	٧
V_{GS}	gate-source voltage		-9	+13	٧
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[2]	-	225	°C

^[1] Specified over lifetime at maximum operating temperature.

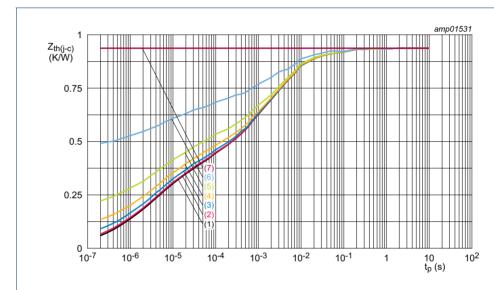
^[2] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 90 ^{\circ}C; P_{L} = 35 W$	0.92	K/W
() -/		T_{case} = 90 °C; t_p = 100 μs ; δ = 10 %	0.48	K/W

- [1] $R_{th(j-c)}$ is measured under RF conditions.
- [2] See Figure 1.



- (1) $\delta = 1 \%$
- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.3 \text{ mA}$	203	209	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 20 \text{ V}; I_D = 30 \text{ mA}$	1.5	2.1	2.5	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 65 V	-	-	1.2	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 20 \text{ V}$	-	4.6	-	Α
I _{GSS}	gate leakage current	V _{GS} = 13 V; V _{DS} = 0 V	-	-	120	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.05 \text{ A}$	-	1.6	-	Ω

Table 7. AC characteristics

 $T_i = 25$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	0.087	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	48.39	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	14.22	-	pF

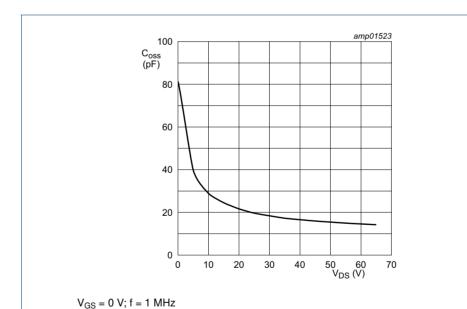


Fig 2. Output capacitance as a function of drain-source voltage; typical values

Table 8. RF characteristics

Test signal: CW pulsed; t_p = 100 μ s; δ = 10 %; f = 108 MHz; RF performance at V_{DS} = 65 V; I_{Dq} = 20 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 35 W	29	31	-	dB
RLin	input return loss	P _L = 35 W	-	-24	-9	dB
η_{D}	drain efficiency	P _L = 35 W	67	70.5	-	%

ART35FE

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Application information

7.1 Application circuit f = 10 MHz to 54 MHz

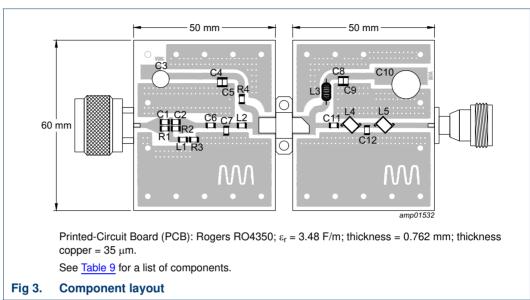
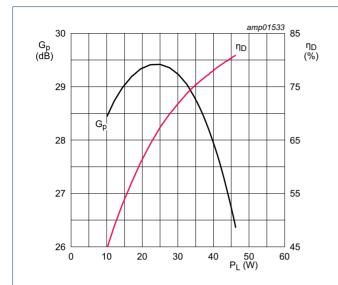


Table 9. List of components For test circuit see Figure 3.

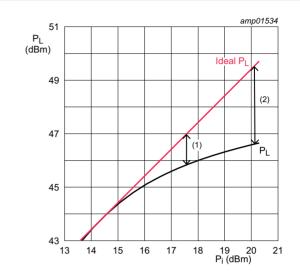
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	2 × 910 pF	ATC 800B
C2	multilayer ceramic chip capacitor	2 × 620 pF	ATC 800B
C3	electrolytic capacitor	47 μF	
C4, C9	multilayer ceramic chip capacitor	4.7 μF, 100 V	
C5, C6, C8, C11	multilayer ceramic chip capacitor	100 nF, 100 V	
C7	multilayer ceramic chip capacitor	30 pF	ATC 800A
C10	electrolytic capacitor	220 μF, 100 V	
C12	multilayer ceramic chip capacitor	24 pF	ATC 800B
R1, R2	chip resistor	2.4 Ω	SMD 1206
R3	chip resistor	43 Ω	SMD 1206
R4	chip resistor	5.1 kΩ	SMD 1206
L1	chip inductor	270 nH	1206CS
L2	chip inductor	68 nH	1206CS
L3	toroid inductor	18 turns, D = 5 mm	0.8 mm copper wire, Ferrite: FT-50-43
L4	air core inductor	68 nH	1812SMS
L5	air core inductor	22 nH	1812SMS

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 V_{DS} = 65 V; I_{Dq} = 10 mA; f = 32 MHz; CW.

Fig 4. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 65 V; I_{Dq} = 10 mA; f = 32 MHz; CW.

- (1) $P_{L(1dB)} = 45.7 \text{ dBm } (37.4 \text{ W})$
- (2) $P_{L(3dB)} = 46.6 \text{ dBm } (46.3 \text{ W})$

Fig 5. Output power as a function of input power; typical values

7.2 Application circuit f = 60 MHz to 130 MHz

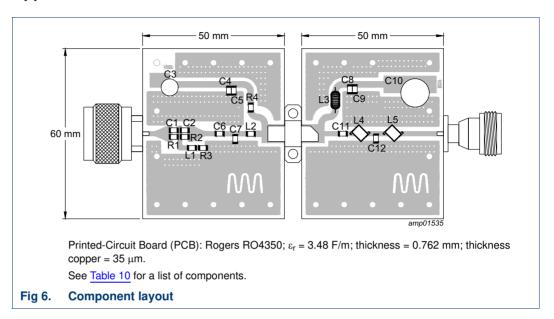
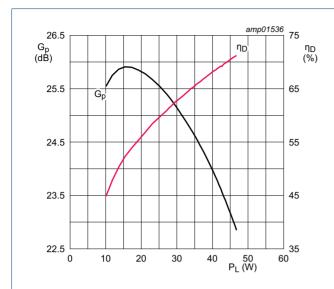


Table 10. List of components

For test circuit see Figure 6.

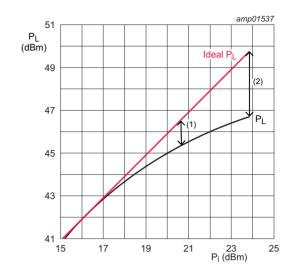
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	2 × 910 pF	ATC 800B
C2	multilayer ceramic chip capacitor	2 × 620 pF	ATC 800B
C3	electrolytic capacitor	47 μF	
C4, C9	multilayer ceramic chip capacitor	4.7 μF, 100 V	
C5, C6, C8, C11	multilayer ceramic chip capacitor	100 nF, 100 V	
C7	multilayer ceramic chip capacitor	30 pF	ATC 800A
C10	electrolytic capacitor	220 μF, 100 V	
C12	multilayer ceramic chip capacitor	24 pF	ATC 800B
R1, R2	chip resistor	2.4 Ω	SMD 1206
R3	chip resistor	43 Ω	SMD 1206
R4	chip resistor	5.1 kΩ	SMD 1206
L1	chip inductor	270 nH	1206CS
L2	chip inductor	68 nH	1206CS
L3	air core inductor	10 turns; D = 5 mm	0.8 mm copper wire
L4	air core inductor	68 nH	1812SMS
L5	air core inductor	22 nH	1812SMS

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 V_{DS} = 65 V; I_{Dq} = 10 mA; f = 95 MHz; CW.

Fig 7. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 65 \text{ V}; I_{Dq} = 10 \text{ mA}; f = 95 \text{ MHz}; CW.$

- (1) $P_{L(1dB)} = 45.2 \text{ dBm } (33.3 \text{ W})$
- (2) $P_{L(3dB)} = 46.7 \text{ dBm } (46.8 \text{ W})$

Fig 8. Output power as a function of input power; typical values

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7.3 Application circuit f = 81 MHz to 108 MHz

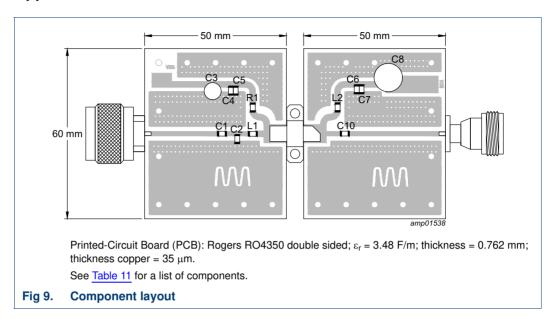


Table 11. List of components

For test circuit see Figure 9.

Component	Description	Value	Remarks
C1, C5, C6	multilayer ceramic chip capacitor	100 nF, 100 V	
C2	multilayer ceramic chip capacitor	56 pF	ATC 800B
C3	electrolytic capacitor	47 μF	
C4. C7	electrolytic capacitor	4.7 μF, 100 V	
C8	multilayer ceramic chip capacitor	220 μF, 100 V	
C10	multilayer ceramic chip capacitor	1000 pF	ATC 800B
R1	chip resistor	5.1 kΩ	SMD 1206
L1	air core inductor	100 nH	1812SMS
L2	air core inductor	90 nH	2222SQ

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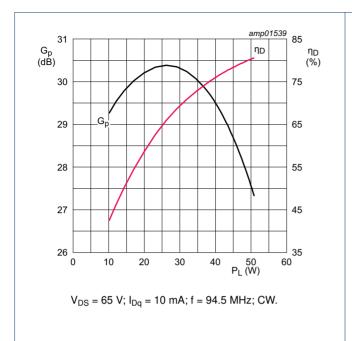
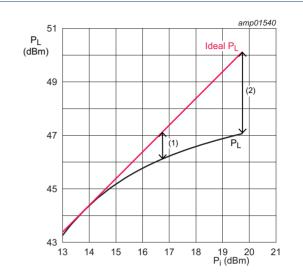


Fig 10. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 65 \text{ V}; I_{Dq} = 10 \text{ mA}; f = 94.5 \text{ MHz}; CW.$

- (1) $P_{L(1dB)} = 46.1 \text{ dBm } (41.2 \text{ W})$
- (2) $P_{L(3dB)} = 47.1 \text{ dBm } (50.9 \text{ W})$

Fig 11. Output power as a function of input power; typical values

8. Test information

8.1 Ruggedness in class-AB operation

The ART35FE is capable of withstanding a load mismatch corresponding to VSWR = $65 \ge 1$ through all phases under the following conditions: $V_{DS} = 65 \text{ V}$; $I_{D\alpha} = 20 \text{ mA}$; $P_L = 35 \text{ W}$; f = 108 MHz; CW and CW pulsed ($t_p = 100 \text{ }\mu\text{s}$; $\delta = 10 \text{ }\%$).

8.2 Impedance information

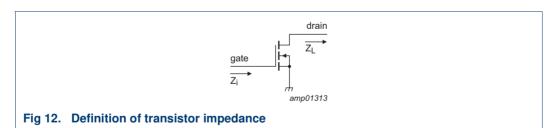


Table 12. Typical push-pull impedance Simulated Z_i and Z_L device impedance.

f	Zi	Z _L	PL			
(MHz)	(Ω)	(Ω)	(W)			
V _{DS} = 65 V	V _{DS} = 65 V					
108	10.4 – j52.5	38.7 + j28.8	35			
V _{DS} = 35 V						
108	10.4 – j52.5	36.4 + j23.0	12			

ART35FE

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8.3 Test circuit

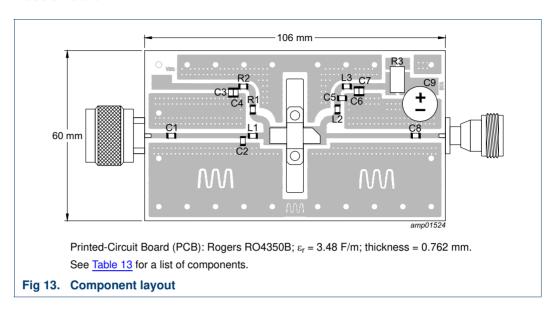


Table 13. List of components

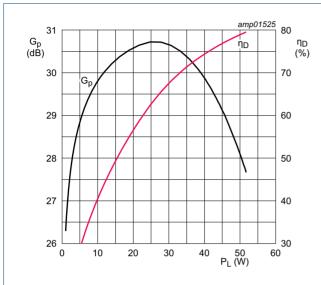
For test circuit see Figure 13.

Component	Description	Value	Remarks
C1, C5, C8	multilayer ceramic chip capacitor	1 nF	ATC100 B
C2	multilayer ceramic chip capacitor	62 pF	ATC100 B
C3, C7	multilayer ceramic chip capacitor	4.7 μF, 100 V	GRM31CC72A475KE11L
C4, C6	multilayer ceramic chip capacitor	0.1 μF, 100 V	GRM188R72A104KA35D
C9	electrolytic capacitor	470 μF, 100 V	
R1	resistor	5 kΩ	SMD 1206
R2	resistor	0 Ω	SMD 1206
R3	shunt resistor	0.01 Ω	Ohmite: FC4L110R010FER
L1	wirewound ceramic chip inductor	82 nH	1206CS
L2	air core inductor	90 nH	2222SQ
L3	air core inductor	100 nH	1812SMS

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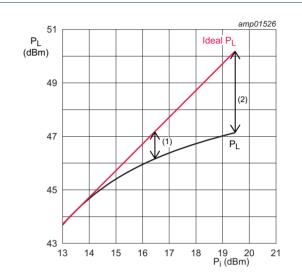
8.4 Graphical data

8.4.1 1-Tone CW



 V_{DS} = 65 V; I_{Dq} = 20 mA; f = 108 MHz.

Fig 14. Power gain and drain efficiency as function of output power; typical values

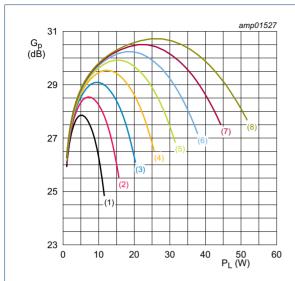


 $V_{DS} = 65 \text{ V}; I_{Dq} = 20 \text{ mA}; f = 108 \text{ MHz}.$

- (1) $P_{L(1dB)} = 46.1 \text{ dBm } (40.8 \text{ W})$
- (2) $P_{L(3dB)} = 47.13 \text{ dBm } (51.7 \text{ W})$

Fig 15. Output power as a function of input power; typical values

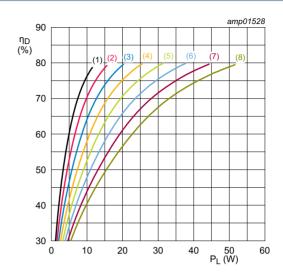
Power LDMOS transistor



 $I_{Dq} = 20 \text{ mA}$; f = 108 MHz.

- (1) $V_{DS} = 30 \text{ V}$
- (2) $V_{DS} = 35 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 45 \text{ V}$
- (5) $V_{DS} = 50 \text{ V}$
- (6) $V_{DS} = 55 \text{ V}$
- (7) $V_{DS} = 60 \text{ V}$
- (8) $V_{DS} = 65 \text{ V}$

Fig 16. Power gain as a function of output power; typical values

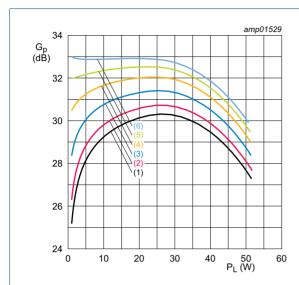


 $I_{Dq} = 20 \text{ mA}$; f = 108 MHz.

- (1) $V_{DS} = 30 \text{ V}$
- (2) $V_{DS} = 35 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 45 \text{ V}$
- (5) $V_{DS} = 50 \text{ V}$
- (6) $V_{DS} = 55 V$
- (7) $V_{DS} = 60 \text{ V}$
- (8) $V_{DS} = 65 \text{ V}$

Fig 17. Drain efficiency as a function of output power; typical values

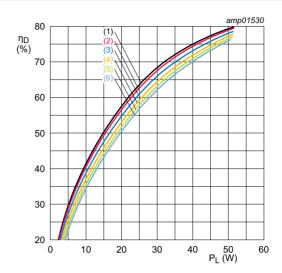
Power LDMOS transistor



 $V_{DS} = 65 \text{ V}; f = 108 \text{ MHz}.$

- (1) $I_{Dq} = 10 \text{ mA}$
- (2) $I_{Dq} = 20 \text{ mA}$
- (3) $I_{Dq} = 50 \text{ mA}$
- (4) $I_{Dq} = 100 \text{ mA}$
- (5) $I_{Dq} = 150 \text{ mA}$
- (6) $I_{Dq} = 200 \text{ mA}$

Fig 18. Power gain as a function of output power; typical values



 $V_{DS} = 65 \text{ V}; f = 108 \text{ MHz}.$

- (1) $I_{Dq} = 10 \text{ mA}$
- (2) $I_{Dq} = 20 \text{ mA}$
- (3) $I_{Dq} = 50 \text{ mA}$
- (4) $I_{Dq} = 100 \text{ mA}$
- (5) $I_{Dq} = 150 \text{ mA}$
- (6) $I_{Dq} = 200 \text{ mA}$

Fig 19. Drain efficiency as a function of output power; typical values

9. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads

SOT467C

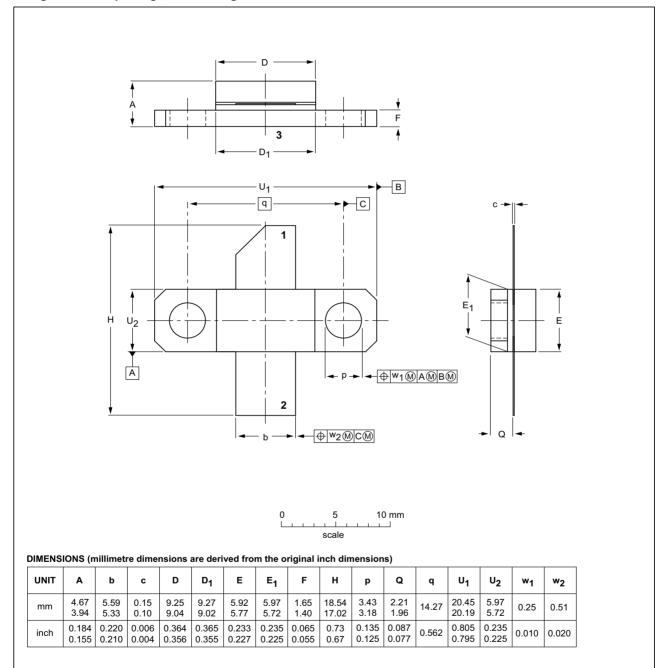


Fig 20. Package outline SOT467C

IEC

OUTLINE

VERSION

SOT467C

EIAJ

ISSUE DATE

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12-05-02

EUROPEAN

PROJECTION

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REFERENCES

JEDEC

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10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

11. Abbreviations

Table 15. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
FM	Frequency Modulation
ISM	Industrial, Scientific and Medical
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MRI	Magnetic Resonance Imaging
MTF	Median Time to Failure
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
UHF	Ultra High Frequency
VHF	Very High Frequency
VSWR	Voltage Standing Wave Ratio

12. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ART35FE v.2	20220708	Product data sheet	-	ART35FE v.1
Modifications:	<u>Section 1.2 on page 1</u> : first list item, changed value drain-source voltage			
	Table 4 on page 2	changed values gate-source	voltage	
	<u>Table 6 on page 4</u> : changed value gate-source voltage			
	Section 13.2 on page 17: updated section			
	Section 13.3 on page 17: updated section			
ART35FE v.1	20201207	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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Power LDMOS transistor

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